## NSN 5961-00-567-9526

Diode Semiconductor Device - Page 1 of 1



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View Online at https://aerobasegroup.com/nsn/5961-00-567-9526
Inclosure Material:
Ceramic
Overall Length:
Between 0.190 inches and 0.210 inches
Overall Diameter:
Between 0.078 inches and 0.084 inches
Mounting Method:
Compression
Semiconductor Material:
Silicon
Voltage Rating In Volts Per Characteristic:
4.0 breakdown voltage, dc
Power Rating Per Characteristic:
2.0 watts small-signal output power, common-base megawatts and 100.0 milliwatts small-signal input power, common-collector of standard
range and 100.0 milliwatts small-signal input power, common-collector absolute
Maximum Operating Tempurature Per Measurement Point:
150.0 degrees celsius ambient air
Precious Material And Location:
Contacts plated gold
Precious Material:
Gold
Test Data Document:
30890-42-004054 drawing (this is the basic governing drawing, such as a contractor drawing, original equipment manufacturer drawing,
etc.; excludes any specification, standard or other document that may be referenced in a basic governing drawing)
Terminal Type And Quantity:
2 ferrule
Shelf Life:
N/a
Unit Of Measure:
Demilitarization:
Yes - demil/mli
Fiig:
A110a0